ELSEVIER

Journal of Crystal Growth 182 (1997) 493–497

JOURNAL OF CRYSTAL GROWTH

Author index

Alvarez, A.L., see Valtueña, J.F. 182 (1997) 281
Aquilano, D., M. Rubbo, M. Catti and A. Pavese, Theoretical equilibrium and growth morphology of $CaCO_3$ polymorphs. I. Aragonite 182 (1997) 168
Ardhuin, H., E. Snoeck and M.-J. Casanove, Epitaxial growth of magnetic Au/Co/Au sandwiches studied by TEM 182 (1997) 394
Asahi, H., see Yamamoto, K. 182 (1997) 227

Bak, R.H., see Lee, Y.K. 182 (1997) 81
BelBruno, J.J., see Ni, J. 182 (1997) 321
Bishop, S.G., see Myoung, J.M. 182 (1997) 241
Björketun, L.-O., L. Hultman, I.P. Ivanov, Q. Wahab and J.-E. Sundgren, Interfacial void formation during vapor phase growth of 3C-SiC on Si(0 0 1) and Si(1 1 1) substrates. Characterization by transmission electron microscopy 182 (1997) 379
Bousquet, V., see Vennéguès, P. 182 (1997) 45

Calle, F., see Valtueña, J.F. 182 (1997) 281
Calleja, E., see Valtueña, J.F. 182 (1997) 281
Carluccio, R., see Friligkos, S. 182 (1997) 341
Casanove, M.-J., see Ardhuin, H. 182 (1997) 394
Catti, M., see Aquilano, D. 182 (1997) 168
Chait, A., see Pines, V. 182 (1997) 219
Cheng, Zh.X., see Yu, X.L. 182 (1997) 428
Choi, I.-H., see Kuroda, K. 182 (1997) 230
Choi, I.-H., see Lee, I.-H. 182 (1997) 309
Choi, I.-H., see Lee, I.-H. 182 (1997) 314
Choi, J.-H., see Lee, T.-W. 182 (1997) 299
Chung, H., see Palosz, W. 182 (1997) 37
Chung, S.J., see Lee, Y.K. 182 (1997) 81
Cina, S., see Friligkos, S. 182 (1997) 341
Clausse, D., see Komunjer, L. 182 (1997) 205

Dalas, E., see Manoli, F. 182 (1997) 116
Daudin, B. and F. Widmann, Layer-by- layer growth of AlN and GaN by molecular beam epitaxy 182 (1997) 1
De Yoreo, J.J., T.A. Land, L.N. Rashkovich, T.A. Onischenko, J.D. Lee, O.V. Monovskii and N.P. Zaitseva, The effect of dislocation cores on growth hillock vicinality and normal growth rates of KDP {1 0 1} surfaces 182 (1997) 442
Diesner, K., see Ellmer, K. 182 (1997) 389
Dorozhkin, S.V., Acidic dissolution mechanism of natural fluorapatite. I. Milli- and microlevels of investigations 182 (1997) 125
Dorozhkin, S.V., Acidic dissolution mechanism of natural fluorapatite. II. Nanolevel of investigations 182 (1997) 133
Dost, S., see Motogaito, A. 182 (1997) 275
Dudley, M., see Palosz, W. 182 (1997) 37

Einarsrud, M.-A., A.M. Mardal Moe and S. Julsrud, Growth and characterisation of $YBa_2Cu_3O_{7-x}$ high T_c superconducting crystals 182 (1997) 363
Ellmer, K., C. Stock, K. Diesner and I. Sieber, Deposition of $c_\perp$-oriented tungsten disulfide (WS_2) films by reactive DC magnetron sputtering from a W-target in Ar/H_2S 182 (1997) 389
Ester, G.R., R. Price and P.J. Halfpenny, An atomic force microscopic investigation of surface degradation of potassium hydrogen phthalate (KAP) crystals caused by removal from solution 182 (1997) 95

Fabietti, L.M. and R. Trivedi, Development of interface morphologies in the tert butyl alcohol–water system 182 (1997) 185
Faurie, J.P., see Vennéguès, P. 182 (1997) 45
Fortunato, G., see Friligkos, S. 182 (1997) 341
Friligkos, S., V. Papaioannou, J. Stoemenos, R. Carluccio, S. Cina and G. Fortunato, Structural characterization of α-Si films crystallized by combined furnace and laser annealing 182 (1997) 341
Fukuda, T., see Uda, S. 182 (1997) 403
Furuhata, N., see Shiraishi, Y. 182 (1997) 255

García, R., see Valtueña, J.F. 182 (1997) 281
García-Ruiz, J.M., see Otálora, F. 182 (1997) 141

García-Ruiz, J.M. and F. Otálora, Crystal growth studies in microgravity with the APCF. II. Image analysis studies 182 (1997) 155
Gillies, D., see Palosz, W. 182 (1997) 37
Gluschenkov, O., see Myoung, J.M. 182 (1997) 241
Gonda, S., see Yamamoto, K. 182 (1997) 227
Gonzalez, V., see López-Acevedo, V. 182 (1997) 103
Goodhew, P.J., see Valtueña, J.F. 182 (1997) 281
Grasza, K., see Palosz, W. 182 (1997) 37
Grützmacher, D., Effect of boron-doping on the growth rate of atmospheric pressure chemical vapour deposition of Si 182 (1997) 53
Grzegory, I., see Weyher, J.L. 182 (1997) 17

Habuka, H., M. Katayama, M. Shimada and K. Okuyama, Nonlinear increase in silicon epitaxial growth rate in a $SiHCl_3$–H_2 system under atmospheric pressure 182 (1997) 352
Halfpenny, P.J., see Ester, G.R. 182 (1997) 95
Hata, M., see Tsuda, M. 182 (1997) 65
Horton, M.N., see Safvi, S.A. 182 (1997) 233
Hosokawa, E., see Tanaka, A. 182 (1997) 60
Hou, W.B., see Yu, X.L. 182 (1997) 428
Hu, J., see Knight, D.G. 182 (1997) 23
Huang, W., Y. Inatomi and K. Kuribayashi, Initial transient solute redistribution during directional solidification with liquid flow 182 (1997) 212
Hultman, L., see Björketun, L.-O. 182 (1997) 379

Ichikawa, J., see Uda, S. 182 (1997) 403
Inaba, K., see Uda, S. 182 (1997) 403
Inatomi, Y., see Huang, W. 182 (1997) 212
Ishibashi, H., see Miyazaki, N. 182 (1997) 73
Ito, H., see Watanabe, N. 182 (1997) 30
Ivanov, I.P., see Björketun, L.-O. 182 (1997) 379
Izpura, I., see Valtueña, J.F. 182 (1997) 281

Julsrud, S., see Einarsrud, M.-A. 182 (1997) 363

Kasatkin, I.A., Effect of induced thermal instability on the growth of mixed crystals from aqueous solution: determination of effective supersaturation and solution composition at the interface 182 (1997) 111
Katayama, M., see Habuka, H. 182 (1997) 352
Katsuno, H., see Motogaito, A. 182 (1997) 275
Kawanaka, T., see Okada, H. 182 (1997) 329
Kelly, G., see Knight, D.G. 182 (1997) 23
Kim, C., see Myoung, J.M. 182 (1997) 241
Kim, D.-Y., see Lee, T.-W. 182 (1997) 299
Kim, K., see Myoung, J.M. 182 (1997) 241
Kim, S., see Myoung, J.M. 182 (1997) 241
Kimura, M., see Motogaito, A. 182 (1997) 275
Kishida, S., see Tanaka, A. 182 (1997) 60
Kloc, Ch., P.G. Simpkins, T. Siegrist and R.A. Laudise, Physical vapor growth of centimeter-sized crystals of α-hexathiophene 182 (1997) 416
Knight, D.G., G. Kelly, J. Hu, S.P. Watkins and M.L.W. Thewalt, Characterization of interfacial dopant layer for high-purity InP grown by MOCVD 182 (1997) 23
Komunjer, L. and B. Mutaftschiev, A quasi two-dimensional bubble method for surface tension and contact angle measurements at the crystal–melt interface. I. Theoretical background 182 (1997) 198
Komunjer, L., D. Clausse and B. Mutaftschiev, A quasi two-dimensional bubble method for surface tension and contact angle measurements at the crystal–melt interface. II. Physical realization 182 (1997) 205
Kon, J., see Uda, S. 182 (1997) 403
Koshizuka, N., see Kuroda, K. 182 (1997) 230
Koutsopoulos, S., see Manoli, F. 182 (1997) 116
Kronsky, N.V., see Rashkovich, L.N. 182 (1997) 434
Kubota, N., M. Yokota and J.W. Mullin, Supersaturation dependence of crystal growth in solutions in the presence of impurity 182 (1997) 86
Kuech, T.F., see Safvi, S.A. 182 (1997) 233
Kurashige, K., see Miyazaki, N. 182 (1997) 73
Kuribayashi, K., see Huang, W. 182 (1997) 212
Kuroda, K., I.-H. Choi, H. Unoki and N. Koshizuka, Erratum to "$NdBa_2Cu_3O_{7-\delta}$ single crystal growth by the traveling-solvent floating-zone method". [J. Crystal Growth 173 (1997) 73] 182 (1997) 230

La Iglesia, A., see López-Acevedo, V. 182 (1997) 103
Land, T.A., see De Yoreo, J.J. 182 (1997) 442
Laudise, R.A., see Kloc, Ch. 182 (1997) 416
Lee, Cheul-Ro, Sung-Jin Son, In-Hwan Lee, Jae-Young Leem and Sam Kyu Noh, Characteristics of $In_xGa_{1-x}N$/GaN grown by LPMOVPE with the variation of growth temperature 182 (1997) 6
Lee, Cheul-Ro, Sung-Jin Son, In-Hwan Lee, Jae-Young Leem and Sam Kyu Noh, High-quality GaN epilayer grown by newly designed horizontal counter-flow MOCVD reactor 182 (1997) 11
Lee, C.-R., see Lee, I.-H. 182 (1997) 309
Lee, C.-R., see Lee, I.-H. 182 (1997) 314
Lee, C.S., see Zhang, Y. 182 (1997) 337
Lee, H.J., H. Ryu and S. Nahm, Formation mechanism of volcano-like structural defects in multiple periods of InAs quantum dots on GaAs 182 (1997) 292
Lee, In-Hwan, see Lee, Cheul-Ro 182 (1997) 6
Lee, In-Hwan, see Lee, Cheul-Ro 182 (1997) 11
Lee, I.-H., I.-H. Choi, C.-R. Lee, S.-J. Son, J.-Y. Leem and S.K. Noh, Effects of hillocks and post-growth annealing on electrical properties in GaN grown by metalorganic chemical vapor deposition 182 (1997) 309

Lee, I.-H., I.-H. Choi, C.-R. Lee, S.-J. Son, J.-Y. Leem and S.K. Noh, Mobility enhancement and yellow luminescence in Si-doped GaN grown by metalorganic chemical vapor deposition technique 182 (1997) 314
Lee, J.D., see De Yoreo, J.J. 182 (1997) 442
Lee, S.-T., see Zhang, Y. 182 (1997) 337
Lee, T.-W., Y.-B. Moon, J.-H. Choi, D.-Y. Kim and E. Yoon, Asymmetric growth behavior of selectively grown InP on vicinal (1 0 0) surfaces by low-pressure metal-organic chemical vapor deposition 182 (1997) 299
Lee, Y.K., R.H. Bak and S.J. Chung, The distribution of inclusions in synthetic quartz 182 (1997) 81
Leem, Jae-Young, see Lee, Cheul-Ro 182 (1997) 6
Leem, Jae-Young, see Lee, Cheul-Ro 182 (1997) 11
Leem, J.-Y., see Lee, I.-H. 182 (1997) 309
Leem, J.-Y., see Lee, I.-H. 182 (1997) 314
Li, G., see Zhang, Y. 182 (1997) 337
Li, H., see Tan, M. 182 (1997) 375
López-Acevedo, V., C. Viedma, V. Gonzalez and A. La Iglesia, Salt crystallization in porous construction materials. II. Mass transport and crystallization processes 182 (1997) 103

MacPherson, G., see Valtueña, J.F. 182 (1997) 281
Manoli, F., S. Koutsopoulos and E. Dalas, Crystallization of calcite on chitin 182 (1997) 116
Mardal Moe, A.M., see Einarsrud, M.-A. 182 (1997) 363
Matyi, R., see Safvi, S.A. 182 (1997) 233
Miyazaki, N., T. Tamura, K. Kurashige, H. Ishibashi and K. Susa, Thermal stress analysis of GSO bulk single crystal 182 (1997) 73
Molina, S.I., see Valtueña, J.F. 182 (1997) 281
Monovskii, O.V., see De Yoreo, J.J. 182 (1997) 442
Moon, Y.-B., see Lee, T.-W. 182 (1997) 299
Motogaito, A., M. Kimura, S. Dost, H. Katsuno, A. Tanaka and T. Sukegawa, Growth of alloy GaInP crystals by compositional conversion of InP layers grown on GaP substrates in an LPE system 182 (1997) 275
Mullan, C.A., G.C. Weatherly and D.A. Thompson, Compositional variations in InGaAsP films grown on patterned substrates 182 (1997) 266
Muller, B., see Vennéguès, P. 182 (1997) 45
Mullin, J.W., see Kubota, N. 182 (1997) 86
Müller, S., see Weyher, J.L. 182 (1997) 17
Mutaftschiev, B., see Komunjer, L. 182 (1997) 198
Mutaftschiev, B., see Komunjer, L. 182 (1997) 205
Myoung, J.M., K.H. Shim, O. Gluschenkov, C. Kim, K. Kim, S. Kim and S.G. Bishop, Effect of growth temperature on the properties of p-type GaN grown by plasma-assisted molecular beam epitaxy 182 (1997) 241

Nahm, S., see Lee, H.J. 182 (1997) 292
Nenow, D. and L. Vitkov, Effect of the opposite directions on the crystal face upon the growth kinetics of weddellite 182 (1997) 461
Nenow, D. and V. Stoyanova, Two-dimensional screw lattice crystal with alternating "surface" structure of the side rows. Equilibrium forms 182 (1997) 465
Ni, J. and J.J. BelBruno, Mechanistic details for dimethylcadmium decomposition and CdS production by MOCVD 182 (1997) 321
Noh, Sam Kyu, see Lee, Cheul-Ro 182 (1997) 6
Noh, Sam Kyu, see Lee, Cheul-Ro 182 (1997) 11
Noh, S.K., see Lee, I.-H. 182 (1997) 309
Noh, S.K., see Lee, I.-H. 182 (1997) 314

Ohmoto, S., see Okada, H. 182 (1997) 329
Okada, H., S. Ohmoto, T. Kawanaka and T. Taguchi, Photoluminescence study of ZnSe single crystals melt-grown with B_2O_3 encapsulant 182 (1997) 329
Okamoto, A., see Shiraishi, Y. 182 (1997) 255
Okuyama, K., see Habuka, H. 182 (1997) 352
Ongaretto, C., see Vennéguès, P. 182 (1997) 45
Onischenko, T.A., see De Yoreo, J.J. 182 (1997) 442
Otálora, F. and J.M. García-Ruiz, Crystal growth studies in microgravity with the APCF. I. Computer simulation of transport dynamics 182 (1997) 141
Otálora, F., see García-Ruiz, J.M. 182 (1997) 155

Pacheco, F.J., see Valtueña, J.F. 182 (1997) 281
Palosz, W., D. Gillies, K. Grasza, H. Chung, B. Raghothamachar and M. Dudley, Characterization of cadmium-zinc telluride crystals grown by 'contactless' PVT using synchrotron white beam topography 182 (1997) 37
Papaioannou, V., see Friligkos, S. 182 (1997) 341
Pavese, A., see Aquilano, D. 182 (1997) 168
Peaker, A.R., see Rutter, P. 182 (1997) 247
Perkins, N.R., see Safvi, S.A. 182 (1997) 233
Pines, V., A. Chait and M. Zlatkowski, Dynamic scaling in dendritic growth: significance of the initial nucleus size 182 (1997) 219
Porowski, S., see Weyher, J.L. 182 (1997) 17
Price, R., see Ester, G.R. 182 (1997) 95

Qi, Z., see Tan, M. 182 (1997) 375

Raghothamachar, B., see Palosz, W. 182 (1997) 37
Rashkovich, L.N. and N.V. Kronsky, Influence of Fe^{3+} and Al^{3+} ions on the kinetics of steps on the $\{1\,0\,0\}$ faces of KDP 182 (1997) 434
Rashkovich, L.N., see De Yoreo, J.J. 182 (1997) 442
Rieke, P.C., Application of Van Oss–Chaudhury–Good theory of wettability to interpretation of interfacial free energies of heterogeneous nucleation 182 (1997) 472

Rubbo, M., see Aquilano, D. 182 (1997) 168
Rutter, P., K.E. Singer and A.R. Peaker, The incorporation of erbium into molecular beam epitaxy grown gallium arsenide 182 (1997) 247
Ryu, H., see Lee, H.J. 182 (1997) 292

Sacedón, A., see Valtueña, J.F. 182 (1997) 281
Safvi, S.A., N.R. Perkins, M.N. Horton, R. Matyi and T.F. Kuech, Effect of reactor geometry and growth parameters on the uniformity and material properties of GaN/sapphire grown by hydride vapor-phase epitaxy 182 (1997) 233
Shibasaki, A., see Tanaka, A. 182 (1997) 60
Shim, K.H., see Myoung, J.M. 182 (1997) 241
Shimada, M., see Habuka, H. 182 (1997) 352
Shimamura, K., see Uda, S. 182 (1997) 403
Shin-no, Y., see Tsuda, M. 182 (1997) 65
Shiraishi, Y., N. Furuhata and A. Okamoto, Selective-area metalorganic molecular beam epitaxy of GaAs using metalorganic chloride gallium precursors 182 (1997) 255
Sieber, I., see Ellmer, K. 182 (1997) 389
Siegrist, T., see Kloc, Ch. 182 (1997) 416
Simpkins, P.G., see Kloc, Ch. 182 (1997) 416
Singer, K.E., see Rutter, P. 182 (1997) 247
Snoeck, E., see Ardhuin, H. 182 (1997) 394
Son, Sung-Jin, see Lee, Cheul-Ro 182 (1997) 6
Son, Sung-Jin, see Lee, Cheul-Ro 182 (1997) 11
Son, S.-J., see Lee, I.-H. 182 (1997) 309
Son, S.-J., see Lee, I.-H. 182 (1997) 314
Stock, C., see Ellmer, K. 182 (1997) 389
Stoemenos, J., see Friligkos, S. 182 (1997) 341
Stoyanova, V., see Nenow, D. 182 (1997) 465
Sukegawa, T., see Motogaito, A. 182 (1997) 275
Sun, Y., see Yu, X.L. 182 (1997) 428
Sundgren, J.-E., see Björketun, L.-O. 182 (1997) 379
Susa, K., see Miyazaki, N. 182 (1997) 73

Taguchi, T., see Okada, H. 182 (1997) 329
Tamura, T., see Miyazaki, N. 182 (1997) 73
Tan, M., B. Xu, H. Li, Z. Qi and Y. Xu, Optimization on the crystal growth of fullerenes 182 (1997) 375
Tanaka, A., S. Kishida, A. Shibasaki, E. Hosokawa and H. Tokutaka, Growth of $Bi_2Sr_2CaCu_2O_y$ single crystals by a vertical Bridgman method and their characterization 182 (1997) 60
Tanaka, A., see Motogaito, A. 182 (1997) 275
Thewalt, M.L.W., see Knight, D.G. 182 (1997) 23
Thompson, D.A., see Mullan, C.A. 182 (1997) 266
Tokutaka, H., see Tanaka, A. 182 (1997) 60
Torii, K., see Yamamoto, M. 182 (1997) 485
Tournié, E., see Vennéguès, P. 182 (1997) 45
Trivedi, R., see Fabietti, L.M. 182 (1997) 185
Tsuda, M., M. Hata and Y. Shin-no, S_A step growth mechanism on (0 0 1) surfaces of diamond structure crystals 182 (1997) 65

Uda, S., J. Kon, K. Shimamura, J. Ichikawa, K. Inaba and T. Fukuda, Interface field-modified solute partitioning during Mn : $LiNbO_3$ crystal fiber growth by micro-pulling down method. II. Radial distribution analysis 182 (1997) 403
Unoki, H., see Kuroda, K. 182 (1997) 230

Valtueña, J.F., A. Sacedón, A.L. Alvarez, I. Izpura, F. Calle, E. Calleja, G. MacPherson, P.J. Goodhew, F.J. Pacheco, R. García and S.I. Molina, Influence of the surface morphology on the relaxation of low-strained $In_xGa_{1-x}As$ linear buffer structures 182 (1997) 281
Vennéguès, P., B. Muller, V. Bousquet, C. Ongaretto, E. Tournié and J.P. Faurie, Microstructural study of pseudomorphic ZnSe films grown on bare GaAs substrates 182 (1997) 45
Viedma, C., see López-Acevedo, V. 182 (1997) 103
Vitkov, L., see Nenow, D. 182 (1997) 461

Wahab, Q., see Björketun, L.-O. 182 (1997) 379
Watanabe, N. and H. Ito, Saturation of hole concentration in carbon-doped GaAs grown by metalorganic chemical vapor deposition 182 (1997) 30
Watkins, S.P., see Knight, D.G. 182 (1997) 23
Weatherly, G.C., see Mullan, C.A. 182 (1997) 266
Weyher, J.L., S. Müller, I. Grzegory and S. Porowski, Chemical polishing of bulk and epitaxial GaN 182 (1997) 17
Widmann, F., see Daudin, B. 182 (1997) 1

Xu, B., see Tan, M. 182 (1997) 375
Xu, Y., see Tan, M. 182 (1997) 375

Yamamoto, K., H. Asahi and S. Gonda, Addendum to "Metalorganic molecular beam epitaxy and etching of GaAs and GaSb using trisdimethylaminoarsenic and trisdimethylaminoantimony". [J. Crystal Growth 145 (1994) 668] 182 (1997) 227
Yamamoto, M. and K. Torii, Theoretical examination for the onset of oscillatory Marangoni convection in liquid bridge 182 (1997) 485
Yokota, M., see Kubota, N. 182 (1997) 86

Yoon, E., see Lee, T.-W. 182 (1997) 299
Yu, X.L., Y. Sun, W.B. Hou, S.J. Zhang and Zh.X. Cheng, Interface kinetics and crystal growth mechanism of a new organometallic coordination compound: triallylthiourea mercury bromide 182 (1997) 428
Zaitseva, N.P., see De Yoreo, J.J. 182 (1997) 442
Zhang, S.J., see Yu, X.L. 182 (1997) 428
Zhang, Y., G. Li, C.S. Lee and S.-T. Lee, Silicon cylinder grown on the surface of a silicon wafer 182 (1997) 337
Zlatkowski, M., see Pines, V. 182 (1997) 219

ELSEVIER

Journal of Crystal Growth 182 (1997) 498–499

JOURNAL OF CRYSTAL GROWTH

Subject index

Apparatus
– for metalorganic chemical vapor deposition
– – by counter-flow reactor
– – – of high quality gallium nitride film 11

Cellular growth
– of tert butyl alcohol 185
Computer simulation
– of epitaxial growth 352
– of protein growth 141, 155
– of thermal stress 73
Constitutional supercooling
– of alpha-hexathiophene 416
Convection 212, 416, 485

Dendritic growth
– of weddelite 461
– theory 219
Device characterization
– electronic materials 299
Diffusional control
– of field modified solute 403
– of ionic solution 103
– of protein growth 141, 155
Dissolution of
– alpha-hexathiophene 416
– barium in lead nitrate 111
– natural apatite 125, 133
– potassium sulphate chromate 111
Doping of
– boron in silicon 53
– carbon in gallium arsenide 30
– erbium in gallium arsenide 247
– silicon in gallium nitride 314

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical 17, 125, 133, 227

Hydrodynamics, see Convection

Kinetics
– of dissolution 125, 133
– of growth 1, 53, 86, 116, 281, 321, 352, 434, 461
– of interface control 428, 461
– of mass transport 141, 155
– of nucleation 116, 309, 375, 461, 472
– of step formation 434

Melt growth technique
– by Bridgman–Stockbarger method
– – of zinc selenide under encapsulation 329
– by Czochralski method
– – of gadolinium orthosilicate 73
– by floating zone method 485
– by micro-pulling down method
– – of lithium niobate 403
– by silicon cylinder grown on silicon wafer 337
– theory of dendritic growth 219
Microgravity, growth under
– of proteins 141, 155
– theory of dendritic growth 219
Morphological stability
– of quantum dots 292
– of surfaces 434
– of tert butyl alcohol 185
– of weddelite 461

Nucleation
– by diffusion in porous media
– – of salts 103
Numbers
– Grashof 416
– Marangoni 485
– Rayleigh 416

Phase diagram, of
– tert butyl alcohol 185
– yttrium barium copper oxide 363
Precursor, for
– gallium arsenide growth 255

Solid growth technique
– by laser annealing
– – of silicon 341

– by recrystallization
– – of silicon 341
Solution growth
– by constant composition method
– – of calcite 116
– by flux method
– – of apatite 125, 133
– – of BSCCO 60
– by hydrothermal growth
– – of synthetic quartz 81
– by low temperature method
– – of barium lead nitrate 111
– – of potassium hydrogen phosphate 442
– – of potassium hydrogen phthalate 95
– – of potassium sulphate chromate 111
– theory
– – of dislocation controlled growth 442
– – of heterogeneous nucleation 472
Stefan problem or moving boundary problem
– of dendritic growth 219
– of solute redistribution 212
Superconductivity materials, high T_c
– bulk
– – of BSCCO 60
– – of YBCO 363
Superlattices
– of gold/cobalt/gold 394
Surface structure
– of screw lattice model crystallization 465

Thin film growth, epitaxy
– by atomic layer epitaxy
– – theory of S_A step growth of diamond 65
– by liquid phase epitaxy
– – of indium gallium phosphide 275
– by metalorganic molecular beam epitaxy
– – of gallium arsenide 255
– by molecular beam epitaxy
– – of aluminum nitride 1
– – of gallium antimonide 227
– – of gallium arsenide 227, 247
– – of gallium nitride 1, 241
– – of indium arsenide 292
– – of indium gallium arsenide 281
– – of indium gallium arsenide phosphide 266
– – of zinc selenide 45
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of gallium nitride 233
– – – of silicon 53, 352
– – – of silicon carbide on silicon 379
– – through metalorganic chemical vapor deposition
– – – of cadmium sulphide 321
– – – of gallium arsenide 30
– – – of gallium nitride 6, 11, 309, 314
– – – of indium gallium nitride 6
– – – of indium phosphide 23, 299

Vapor growth technique
– by chemical transport
– – of gallium nitride 233
– by evaporation and condensation
– – of single crystalline C_{60} 375
– by magnetron sputtering
– – of tungsten disulphide 389
– by physical vapor transport
– – cadmium zinc telluride 37

Whisker growth, of
– aphthitalite 103
– arcanite 103
– epsomite 103
– hexaidrite 103
– mirabilite 103
– picromerite 103
– potassium dchromate 103
– thenardite 103